

**PENDING CLAIMS**

What follows is a complete list of claims currently pending in the application.

Please amend claims 1 and 2 as shown below.

1. (Currently amended) A three dimensional multi-level memory array disposed above a substrate, the array comprising:  
a first plurality of spaced-apart rail-stacks disposed at a first height in a first direction above the substrate;  
a second plurality of spaced-apart rail-stacks disposed above the first height and in a second direction different from the first direction;  
and  
a plurality of memory cells, each memory cell comprising a silicon nitride antifuse,  
wherein the antifuses are disposed at the intersections of the first rail-stacks and the second rail-stacks.
2. (Currently amended) The array of claim 1, further comprising polysilicon p+n-diodes or polysilicon p-n+ diodes.